G8551S PNP EPITAXIAL SILICON TRANSISTOR

LOW VOLTAGE HIGH CURRENT SMALL SIGNAL PNP TRANSISTOR

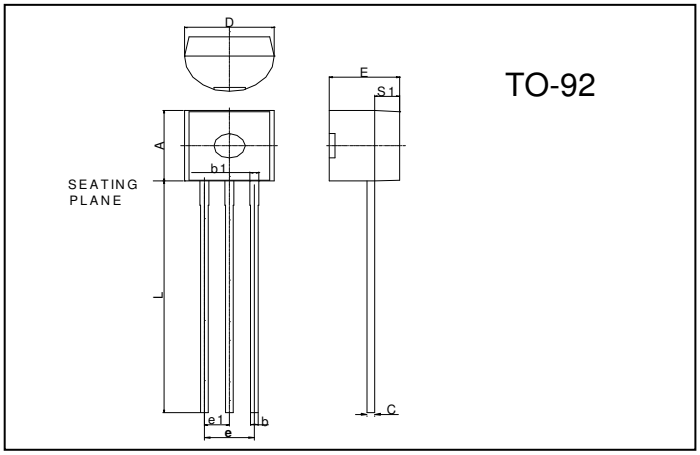
Description

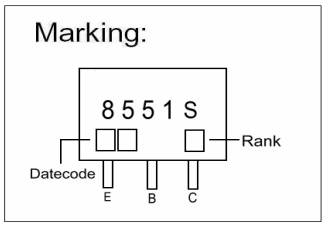
The G8551 is a low voltage high current small signal PNP transistor, designed for Class B push-pull audio amplifier for portable radio and general purpose applications.

Features

*Collector current up to 700mA
*Collector –Emitter voltage up to 20V
*Complimentary to G8051S

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S_1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b_1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

Absolute Maximum Ratings (Ta = 25℃,unless otherwise specified)

Parameter		Ratings	Unit
Collector to Base Voltage	V_{CBO}	-25	V
Collector to Emitter Voltage	V_{CEO}	-20	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collect Current(DC)	I_C	-0.7	A
Junction Temperature	Tj	+150	℃
Storage Temperature Range	T_{STG}	-55 ~ +150	℃
Total Power Dissipation	PD	625	mW

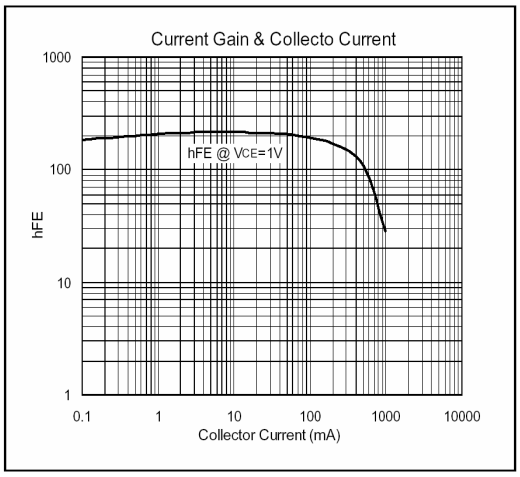
Electrical Characteristics(Ta = 25℃,unless otherwise specified)

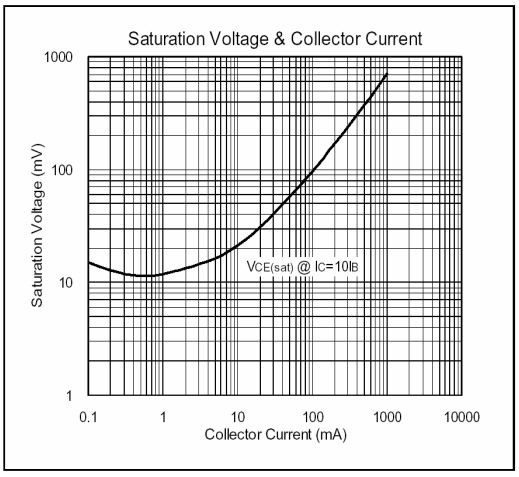
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-25	-	-	V	I_C=-10uA,I_E=0
BV_{CEO}	-20	-	-	V	I_C=-1mA,I_B=0
BV_{EBO}	-5	-	-	V	I_E=-10uA,I_C=0
I_{CBO}	-	-	-1	uA	V_{CB}=-20V, I_E=0
hFE1	100	-	500		V_{CE}=-1V,I_C=-150mA
hFE2	-	100	-		V_{CE}=-1V,I_C=-500mA
$V_{CE(sat)}$	-	-	-0.5	V	I_C=-500mA,I_B=-50mA
$V_{BE(on)}$	-	-	-1	V	V_{CE}=-1V,I_C=-150mA
V_{BE}	-	-	-1.0	V	V_{CE}=-1V,I_C=-10mA
fT	150	-	-	MHz	V_{CE}=-10V,Ic=-20Ma, f=100MHz
Cob	-	10	-	pF	V_{CB}=-10V, I_E=0A,f=1MHz

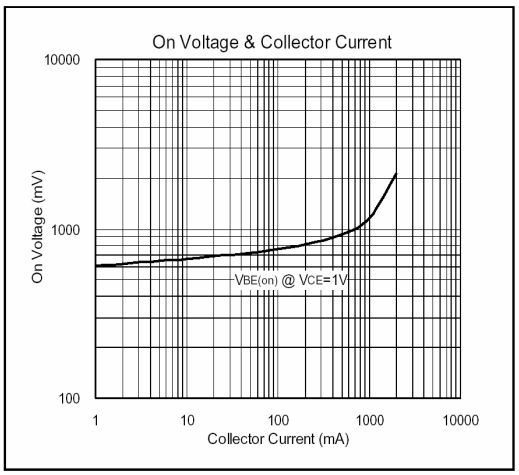
Classification Of h_{FE1}

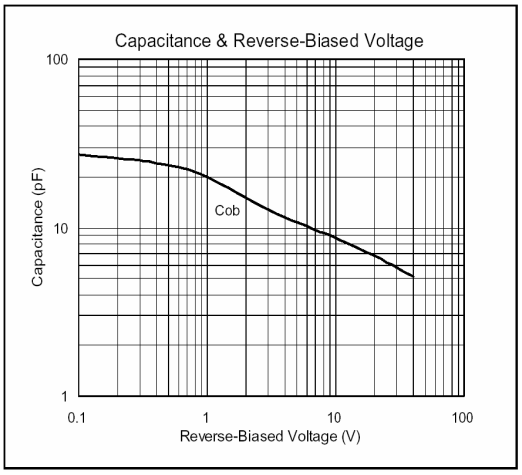
Rank	C	D	E
Range	100-180	160-300	280-500

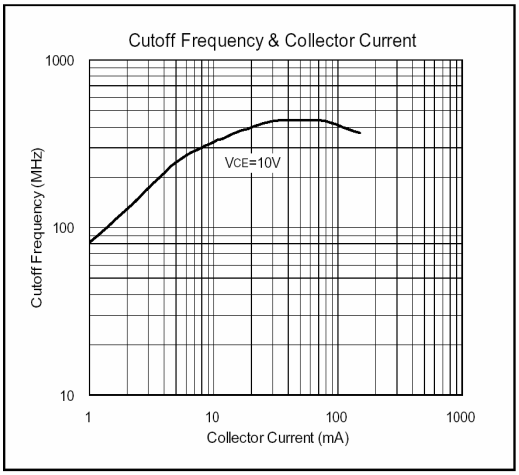
Characteristics Curve

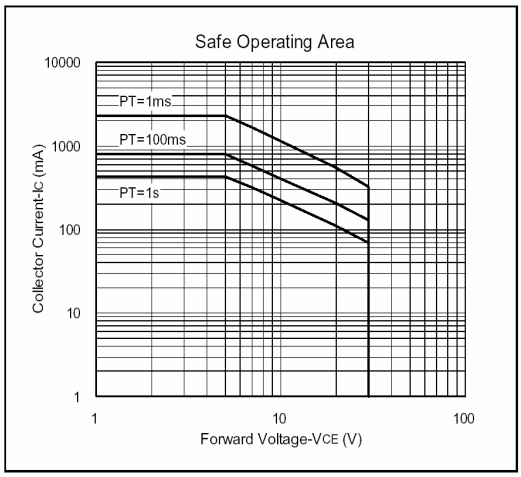












Head Office And Factory:
- **Taiwan**: No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
  TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China**: (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
  TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165